

HUF76145S3ST-VB Datasheet N-Channel 30-V (D-S) MOSFET

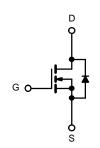
PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^{a, e}	Q _g (Typ)			
30	$0.0024 \text{ at V}_{GS} = 10 \text{ V}$	98	82 nC			
	0.0027 at V _{GS} = 4.5 V	98	02 HC			

FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU







N-Channel MOSFET

APPLICATIONS

- OR-ing
- Server
- DC/DC

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	30	V		
Gate-Source Voltage		V _{GS}	± 20	v	
	T _C = 25 °C		98 ^{a, e}	A	
Continuous Drain Current (T. – 175 °C)	T _C = 70 °C		98 ^e		
Continuous Drain Current (T _J = 175 °C)	T _A = 25 °C	I _D	28.8 ^{b, c}		
	T _A = 70 °C		27 ^{b, c}		
Pulsed Drain Current	I _{DM}	300			
valanche Current Pulse		I _{AS}		36	
Single Pulse Avalanche Energy	L=0.1 IIII	E _{AS}	64.8	V	
Continuous Source-Drain Diode Current	T _C = 25 °C	I.	90 ^{a, e}	^	
Continuous Source-Diairi Diode Current	T _A = 25 °C	I _S	3.13 ^{b, c}	A	
	T _C = 25 °C		250 ^a		
Manifestor Brown Binding for	T _C = 70 °C	В	175	10/	
Maximum Power Dissipation	T _A = 25 °C	P _D	3.75 ^{b, c}	W	
	T _A = 70 °C		2.63 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Тур.	Max.	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 sec	R _{thJA}	32	40	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	0.5	0.6	J/VV	

Notes:

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.

- b. Striate informed on 1 X 1 114 board.
 c. t = 10 sec.
 d. Maximum under steady state conditions is 90 °C/W.
 e. Calculated based on maximum junction temperature. Package limitation current is 90 A.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$ 30				V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		35		1406
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	ι _D = 230 μΑ		- 7.5		mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.5		2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
7 0 0 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1.	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	μA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	90			Α
		V _{GS} = 10 V, I _D = 28.8 A		0.0024		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 27 A		0.0027		Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 28.8 A		160		S
Dynamic ^b			L	L		
Input Capacitance	C _{iss}			12065		
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		1725		pF
Reverse Transfer Capacitance	C _{rss}			970		
Total Gate Charge	Qg	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 28.8 A		171	257	nC
				81.5	123	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 28.8 \text{ A}$		34		
Gate-Drain Charge	Q _{gd}			29		
Gate Resistance	R _g	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	t _{d(on)}			18	27	
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_{I} = 0.625 \Omega$		11	17	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 24 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		70	105	ns
Fall Time	t _f			10	15	
Turn-On Delay Time	t _{d(on)}			55	83	
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_1 = 0.67 \Omega$		180	270	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 22.5 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		55	83	
Fall Time	t _f	Ş		12	18	
Drain-Source Body Diode Characteristic	T T					l
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			90	_
Pulse Diode Forward Current ^a	I _{SM}				90	Α
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			52	78	ns
Body Diode Reverse Recovery Charge	Q _{rr}			70.2	105	nC
Reverse Recovery Fall Time	t _a	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/µs}, T_J = 25 °C$		27		
Reverse Recovery Rise Time	t _b			25		ns

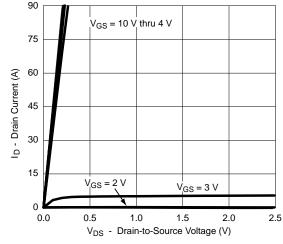
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

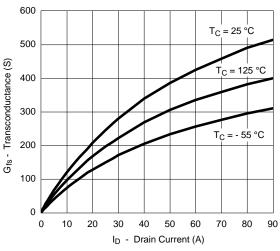
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



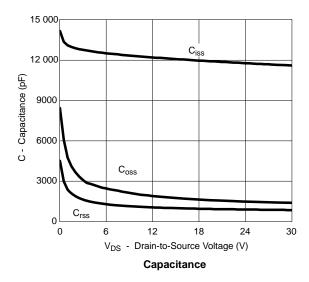
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics

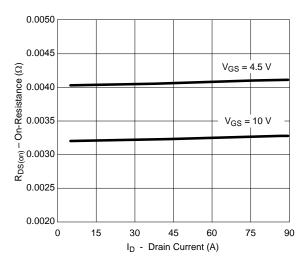


Transconductance

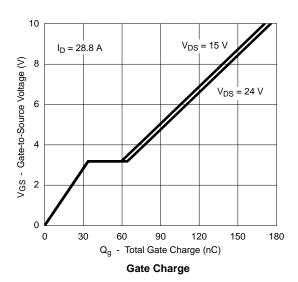




Transfer Characteristics

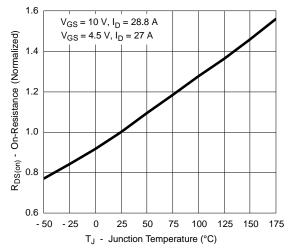


R_{DS(on)} vs. Drain Current

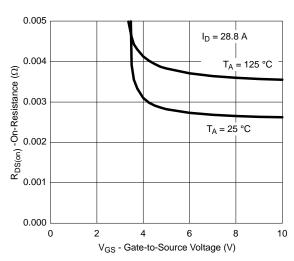




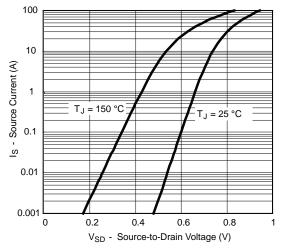
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



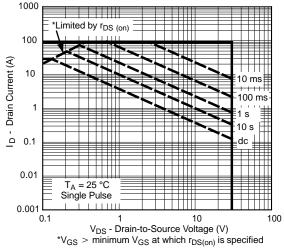
 $R_{DS(on)}$ vs. V_{GS} vs. Temperature



Forward Diode Voltage vs. Temperature



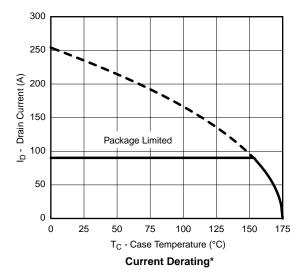
Threshold Voltage



Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





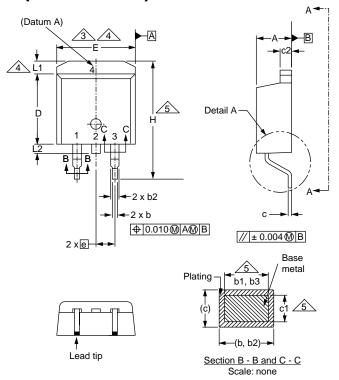
*The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

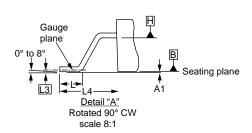


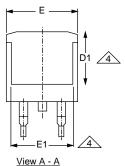
Normalized Thermal Transient Impedance, Junction-to-Case



TO-263AB (HIGH VOLTAGE)







			D1 4
L	E	1	4

	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
Α	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
С	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
Е	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	i
е	2.54 BSC		0.100 BSC	
Н	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010	BSC
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08

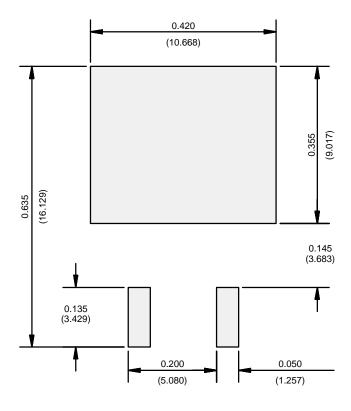
DWG: 5970

Notes

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
- 4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
- 5. Dimension b1 and c1 apply to base metal only.
- 6. Datum A and B to be determined at datum plane H.
- 7. Outline conforms to JEDEC outline to TO-263AB.



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)



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